

BCR12CM-12LA

Triac

Medium Power Use

REJ03G0297-0300 Rev.3.00 Nov 30, 2007

Features

I_{T (RMS)}: 12 A
 V_{DRM}: 600 V

I_{FGTI}, I_{RGTI}, I_{RGT III}: 30 mA $(20 \text{ mA})^{\text{Note6}}$

• Non-Insulated Type

• Planar Passivation Type

Outline

RENESAS Package code: PRSS0004AA-A
(Package name: TO-220)

2, 4

1. T₁ Terminal
2. T₂ Terminal
3. Gate Terminal
4. T₂ Terminal

Applications

Contactless AC switch, light dimmer, electronic flasher unit, control of household equipment such as TV sets, stereo systems, refrigerator, washing machine, infrared kotatsu, carpet, electric fan, and solenoid driver, small motor control, copying machine, electric tool, electric heater control, and other general purpose control applications

Maximum Ratings

Parameter	Symbol	Voltage class	Unit
r al allietei	Symbol	12	Onit
Repetitive peak off-state voltage ^{Note1}	V_{DRM}	600	V
Non-repetitive peak off-state voltage ^{Note1}	V_{DSM}	720	V

Parameter	Symbol	Ratings	Unit	Conditions
RMS on-state current	I _{T (RMS)}	12	А	Commercial frequency, sine full wave 360° conduction, Tc = 98°C ^{Note3}
Surge on-state current	I _{TSM}	120	А	60Hz sinewave 1 full cycle, peak value, non-repetitive
I ² t for fusing	l ² t	60	A ² s	Value corresponding to 1 cycle of half wave 60Hz, surge on-state current
Peak gate power dissipation	P _{GM}	5	W	
Average gate power dissipation	P _{G (AV)}	0.5	W	
Peak gate voltage	V_{GM}	10	V	
Peak gate current	I _{GM}	2	Α	
Junction temperature	Tj	- 40 to +125	°C	
Storage temperature	Tstg	- 40 to +125	°C	
Mass	_	2.0	g	Typical value

Notes: 1. Gate open.

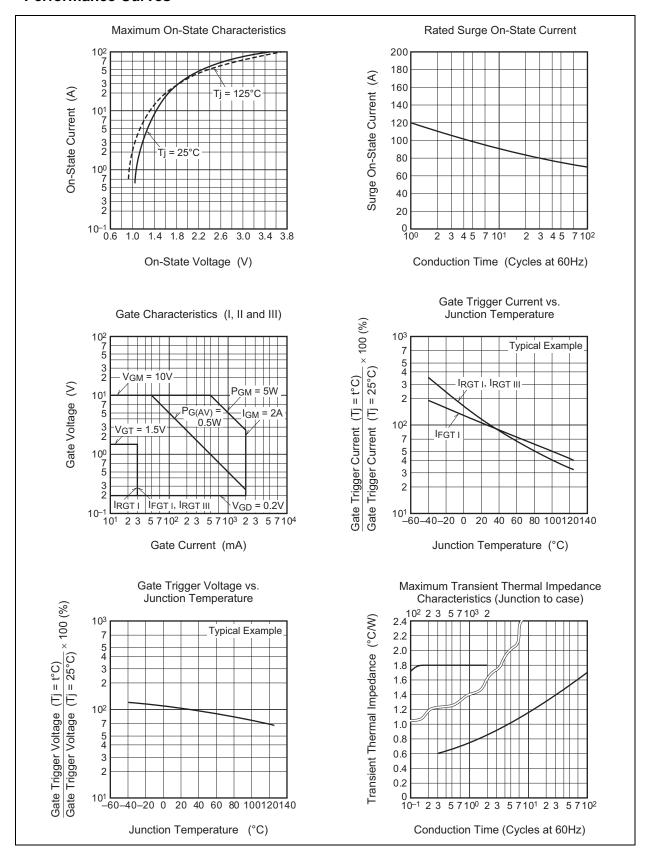
Electrical Characteristics

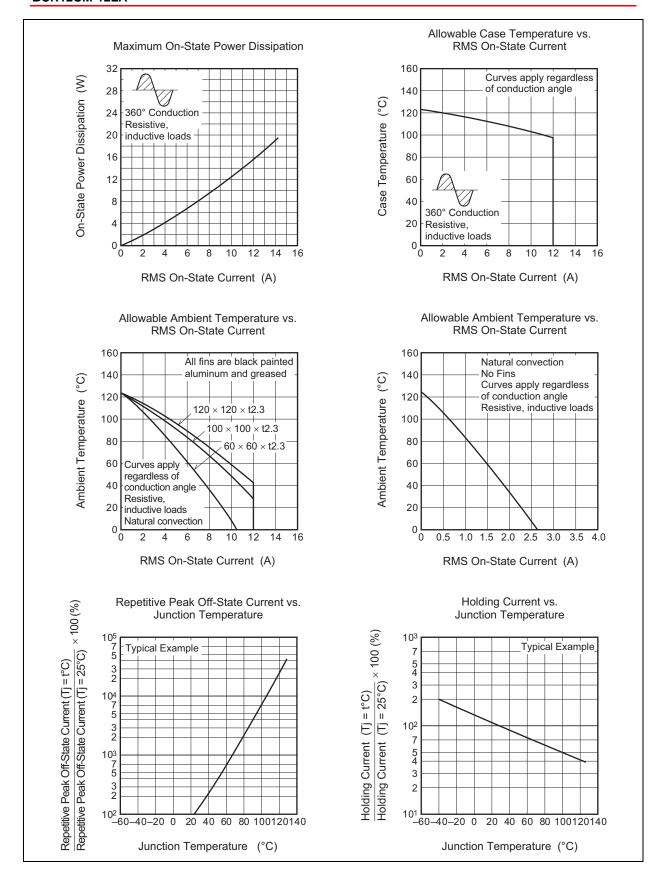
Parameter		Symbol	Min.	Тур.	Max.	Unit	Test conditions
Repetitive peak off-state curr	rent	I _{DRM}	_	_	2.0	mA	Tj = 125°C, V _{DRM} applied
On-state voltage		V_{TM}	_	_	1.6	V	Tc = 25°C, I _{TM} = 20 A, Instantaneous measurement
Gate trigger voltage ^{Note2}	I	$V_{FGT_{I}}$	_	_	1.5	V	$Tj = 25^{\circ}C, V_D = 6 V, R_L = 6 \Omega,$
	II	$V_{RGT_{I}}$		_	1.5	>	$R_G = 330 \Omega$
	III	V_{RGTIII}	_	_	1.5	V	
Gate trigger current ^{Note2}	I	I_{FGTI}	_	_	30 ^{Note6}	mA	$Tj = 25$ °C, $V_D = 6$ V, $R_L = 6$ Ω,
	II	I_{RGTI}		_	30 ^{Note6}	mA	$R_G = 330 \Omega$
	III	I_{RGTIII}	_	_	30 ^{Note6}	mA	
Gate non-trigger voltage		V_{GD}	0.2	_	_	V	Tj = 125°C, V _D = 1/2 V _{DRM}
Thermal resistance		R _{th (j-c)}	_	_	1.8	°C/W	Junction to case Note3 Note4
Critical-rate of rise of off-stat commutating voltage ^{Note5}	е	(dv/dt)c	10	_	_	V/µs	Tj = 125°C

- Notes: 2. Measurement using the gate trigger characteristics measurement circuit.
 - 3. Case temperature is measured at the T_2 tab 1.5 mm away from the molded case.
 - 4. The contact thermal resistance $R_{th\,(c\text{-}f)}$ in case of greasing is 1.0°C/W.
 - 5. Test conditions of the critical-rate of rise of off-state commutating voltage is shown in the table below.
 - 6. High sensitivity ($I_{GT} \le 20$ mA) is also available. (I_{GT} item: 1)

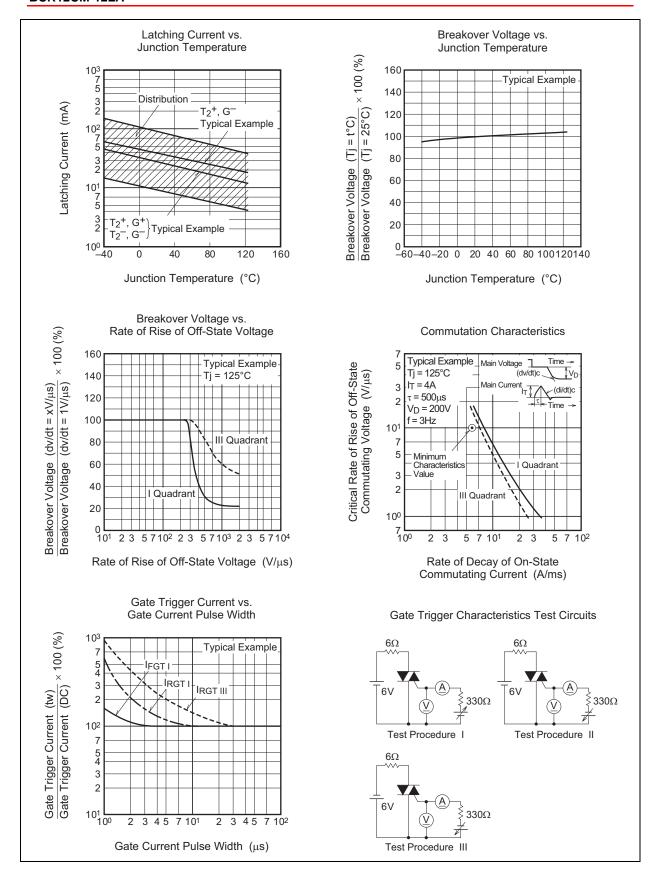
Test conditions	Commutating voltage and current waveforms (inductive load)
1. Junction temperature Tj = 125°C	Supply Voltage → Time
2. Rate of decay of on-state commutating current (di/dt)c = - 6.0 A/ms	Main Current (di/dt)c → Time
3. Peak off-state voltage $V_D = 400 \text{ V}$	Main Voltage Time (dv/dt)c

Performance Curves

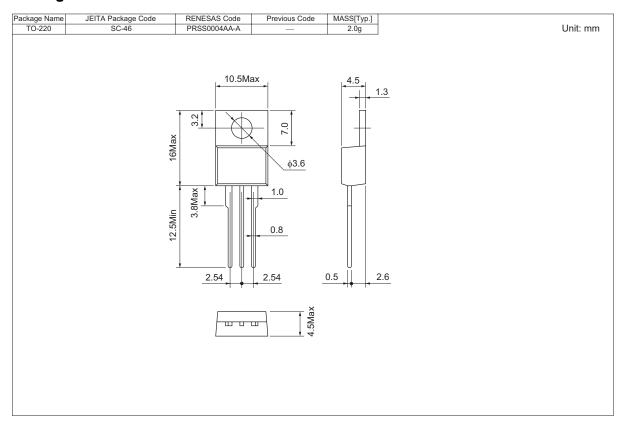




RENESAS



Package Dimensions



Order Code

Lead form	Standard packing	Quantity	Standard order code	Standard order code example
Straight type	Vinyl sack	100	Type name	BCR12CM-12LA
Lead form	Plastic Magazine (Tube)	50	Type name – Lead forming code	BCR12CM-12LA-A8

Note: Please confirm the specification about the shipping in detail.

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 Notes:

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